L Number	Hits	Search Text	DB	Time stamp
Number 7	54	257/\$.ccls. and capacitor and pillar and	USPAT;	2002/09/26
,	73	(metal copper aluminum) same (storage	US-PGPUB;	08:38
		lower) adj (electrode node)	EPO; JPO;	00.30
		lower, and (erectrone none)	DERWENT	
_	399	semiconductor and DRAM and capacitor same	USPAT;	2002/09/25
_	399	pillar	US-PGPUB;	14:43
		pillar	EPO; JPO;	14.43
			DERWENT	
	9	("4252579" "4833516" "5027172"	USPAT	2002/00/25
-	9	"4252579" "4833516" "5027172" "5055898" "5177576" "5316962"	USPAI	2002/09/25
	•	"5319235" "5350941" "5498584").PN.		13:43
	272		HCDAM.	2002/00/25
_	272	(257/308).CCLS.	USPAT;	2002/09/25
			US-PGPUB;	14:46
			EPO; JPO;	1
	0.5.6	(1057/200)	DERWENT	0000 (00 (05
-	256	((257/308).CCLS.) and @ad<=20001226	USPAT;	2002/09/25
	1		US-PGPUB;	14:50
			EPO; JPO;	
	1		DERWENT	0000 (00 15-
-	241		USPAT;	2002/09/25
		(semiconductor and DRAM and capacitor	US-PGPUB;	15:48
		same pillar)	EPO; JPO;	
			DERWENT	
_	12	5481127.URPN.	USPAT	2002/09/25
				15:03
_	4		USPAT	2002/09/25
-		"5318920").PN.		15:05
	.26	5023683.URPN.	USPAT	2002/09/25
				15:11
-	2	("4785337" "4855801").PN.	USPAT	2002/09/25
				15:17
-	4		USPAT	2002/09/25
		"5318920").PN.		15:17
-	12	5481127.URPN.	USPAT	2002/09/25
				15:18
-	445	(257/309).CCLS.	USPAT;	2002/09/25
	1		US-PGPUB;	15:48
			EPO; JPO; .	
	1		DERWENT	
	341	((257/309).CCLS.) not	USPAT;	2002/09/25
		(((((257/308).CCLS.) and @ad<=20001226)	US-PGPUB;	15:49
		not (semiconductor and DRAM and capacitor	EPO; JPO;	
		same pillar)) (semiconductor and DRAM	DERWENT	
		and capacitor same pillar))		
-	298		USPAT;	2002/09/25
		(((((257/308).CCLS.) and @ad<=20001226)	US-PGPUB;	16:04
		not (semiconductor and DRAM and capacitor	EPO; JPO;	
		same pillar)) (semiconductor and DRAM	DERWENT	
		and capacitor same pillar))) and		
		@ad<=20001226		
-	51	. , ,	USPAT;	2002/09/26
		adj dielectric and metal same storage adj	US-PGPUB;	08:36
		electrode	EPO; JPO;	
			DERWENT	
-	196		USPAT;	2002/09/25
		adj (node electrode) same pillar	US-PGPUB;	16:24
	1		EPO; JPO;	
	1		DERWENT	

_	43	(capacitor and semiconductor and storage	USPAT;	2002/09/25
1		adj (node electrode) same pillar) not	US-PGPUB;	16:25
		((semiconductor and DRAM and capacitor	EPO; JPO;	
		same pillar) ((((257/308).CCLS.) and	DERWENT	ł
		@ad<=20001226) not (semiconductor and		
		DRAM and capacitor same pillar))		
		(((257/309).CCLS.) not		
		(((((257/308).CCLS.) and @ad<=20001226)		
		not (semiconductor and DRAM and capacitor		
		same pillar)) (semiconductor and DRAM		
		and capacitor same pillar)))		
		(257/\$.ccls. and capacitor and capacitor		
		adj dielectric and metal same storage adj		
		electrode))		